

Features

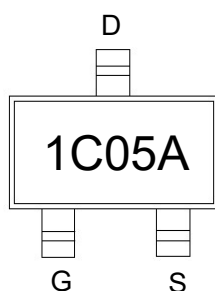
- Trench Power LV MOSFET technology
- High Density Cell Design for Low $R_{DS(ON)}$
- High Speed switching

Product Summary

V_{DS}	$R_{DS(ON)}$ MAX	I_D MAX
120V	150mΩ@10V	5A
	200mΩ@4.5V	

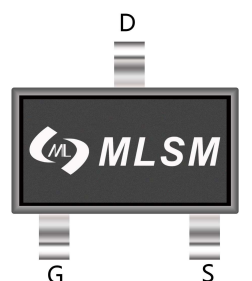
Application

- Load Switch
- Isolated DC/DC convertor

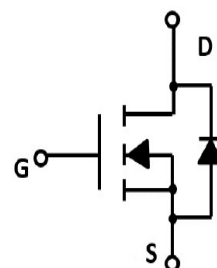


Marking and pin assignment

1C05A: Device code



SOT-23-3L top view



Schematic diagram



Halogen-Free

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Rating	Unit
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Common Ratings (TC=25°C Unless Otherwise Noted)

V_{DS}	Drain-Source Breakdown Voltage	120	V
V_{GS}	Gate-Source Voltage	±20	V
T_J	Maximum Junction Temperature	150	°C
T_{STG}	Storage Temperature Range	-50 to 155	°C
I_S	Diode Continuous Forward Current	$T_c=25^\circ\text{C}$	5
			A

Mounted on Large Heat Sink

I_{DM}	Pulse Drain Current Tested	$T_c=25^\circ\text{C}$	15	A
I_D	Continuous Drain Current	$T_c=25^\circ\text{C}$	5	A
P_D	Maximum Power Dissipation	$T_c=25^\circ\text{C}$	23	W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient		30	°C/W

Ordering Information (Example)

Type	Package	Marking	Minimum Package(pcs)	Inner Box Quantity(pcs)	Outer Carton Quantity(pcs)	Delivery Mode
MLSK1C05A	SOT-23-3L	1C05A	3,000	45,000	180,000	7"reel

Electrical Characteristics (T _J =25°C unless otherwise noted)						
Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ T _J = 25°C (unless otherwise stated)						
B _{V(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	120	–	–	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =120V, V _{GS} =0V	–	–	1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V	–	–	±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.0	1.8	2.5	V
R _{DS(on)}	Drain-Source On-State Resistance	V _{GS} =10V, I _D =5A	–	120	150	mΩ
		V _{GS} =4.5V, I _D =3A	–	130	200	mΩ
Dynamic Electrical Characteristics @ T _J = 25°C (unless otherwise stated)						
C _{ISS}	Input Capacitance	V _{DS} =60V, V _{GS} =0V, f=1MHz	–	1050	–	pF
C _{OSS}	Output Capacitance		–	26	–	pF
C _{RSS}	Reverse Transfer Capacitance		–	20	–	pF
Switching Characteristics						
Q _g	Total Gate Charge	V _{DS} =60V, I _D =5A, V _{GS} =10V	–	23	–	nC
Q _{gs}	Gate Source Charge		–	3.5	–	nC
Q _{gd}	Gate Drain Charge		–	5	–	nC
t _{d(on)}	Turn-on Delay Time	V _{DS} =60V, I _D =5A, V _{GS} =10V, R _G =3Ω	–	10.8	–	nS
t _r	Turn-on Rise Time		–	5.2	–	nS
t _{d(off)}	Turn-Off Delay Time		–	32.6	–	nS
t _f	Turn-Off Fall Time		–	5.8	–	nS
Source- Drain Diode Characteristics						
V _{SD}	Forward on voltage	T _J =25°C, I _S =5A	–	–	1.2	V

Typical Operating Characteristics

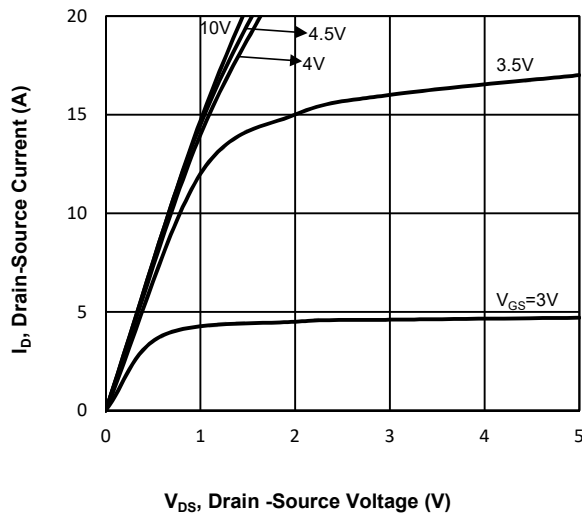


Fig1. Typical Output Characteristics

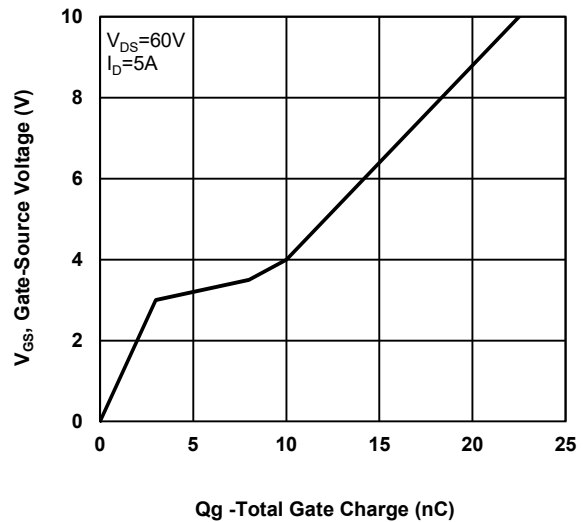


Fig2. Typical Gate Charge Vs. Gate-Source Voltage

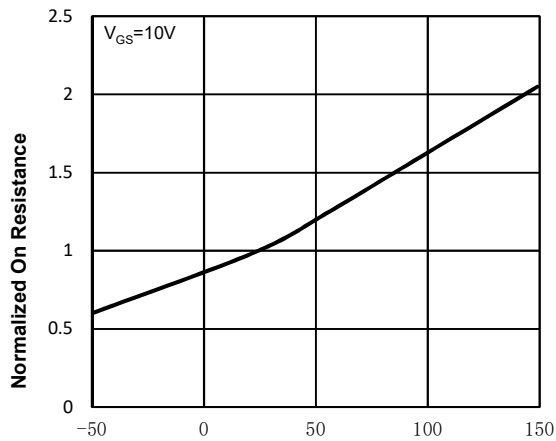


Fig3. Normalized On-Resistance Vs. Temperature

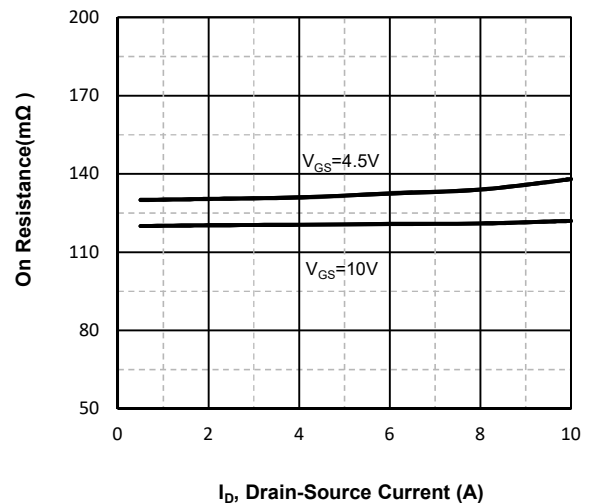


Fig4. On-Resistance Vs. Drain-Source Current

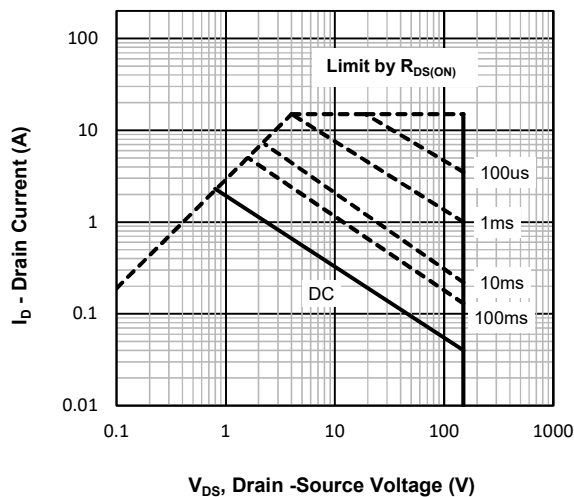


Fig5. Maximum Safe Operating Area

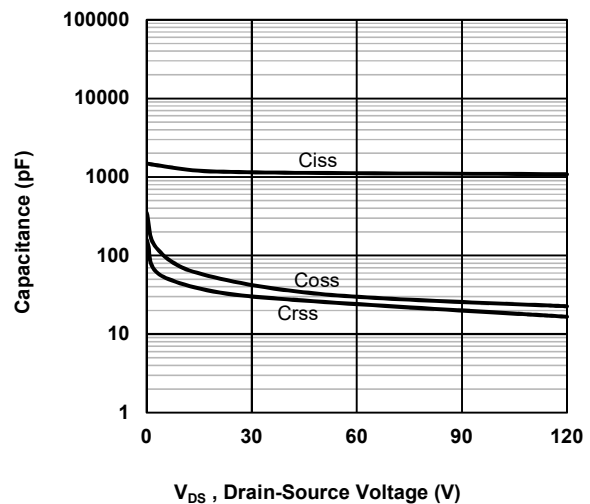
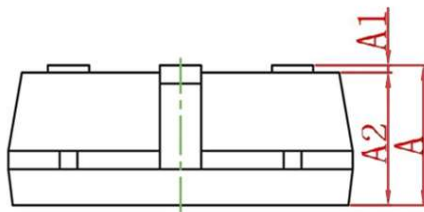
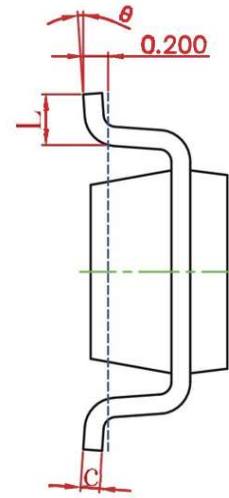
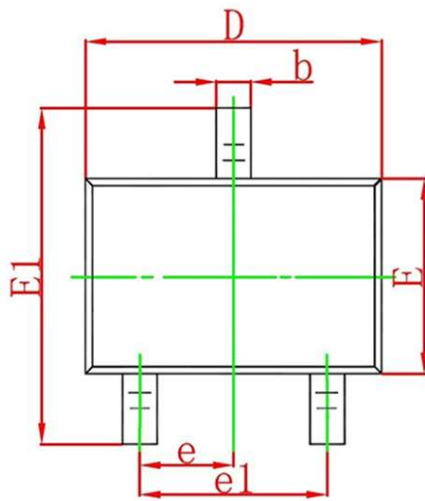


Fig6. Typical Capacitance Vs. Drain-Source Voltage

SOT-23-3L Package information



Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.042	0.050
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.042	0.046
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.112	0.120
E	1.500	1.700	0.060	0.068
E1	2.650	2.950	0.106	0.118
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°